"Yب / Descriptions

TO-220 N MOS

N-CHANNEL MOSFET in a TO-220 Plastic Package.

◕ È / Features

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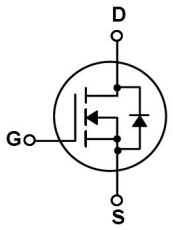
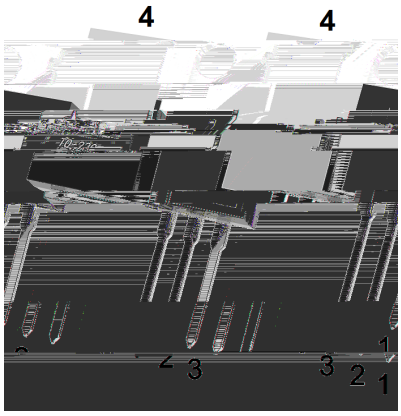
Low gate charge, low crss, fast switching, HF Product.

[redacted]

DC/DC

These devices are well suited for high efficiency switching DC/DC converters, and switch mode power supplies.





PIN1 G PIN 2 4 D PIN 3 S

ł. ʜ ȧ / Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	I_D(Tc=25)	8	A
Drain Current - Pulsed	I_{DM}	32	A
Gate-Source Voltage	V_{GSS}	±30	V
Single Pulsed Avalanche Energy	E_{AS}	597	mJ
Avalanche Current	I_{AR}	10.5	A
Power Dissipation	P_D(Tc=25)	110	W
Operating and Storage Temperature Range	T_J,T_{STG}	-55 to 150	
Thermal resistance, junction- case	R_{dJC}	1.14	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250εA	650	700		V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=650V V_{GS}=0V			1.0	εA
Gate-Body Leakage Current, Forward	I_{GSS}	V_{GS}GSj10.4955 354.5.9 395.7803 Tm1.4429 T5(GS)Tj.48 .0005 Tc1.				

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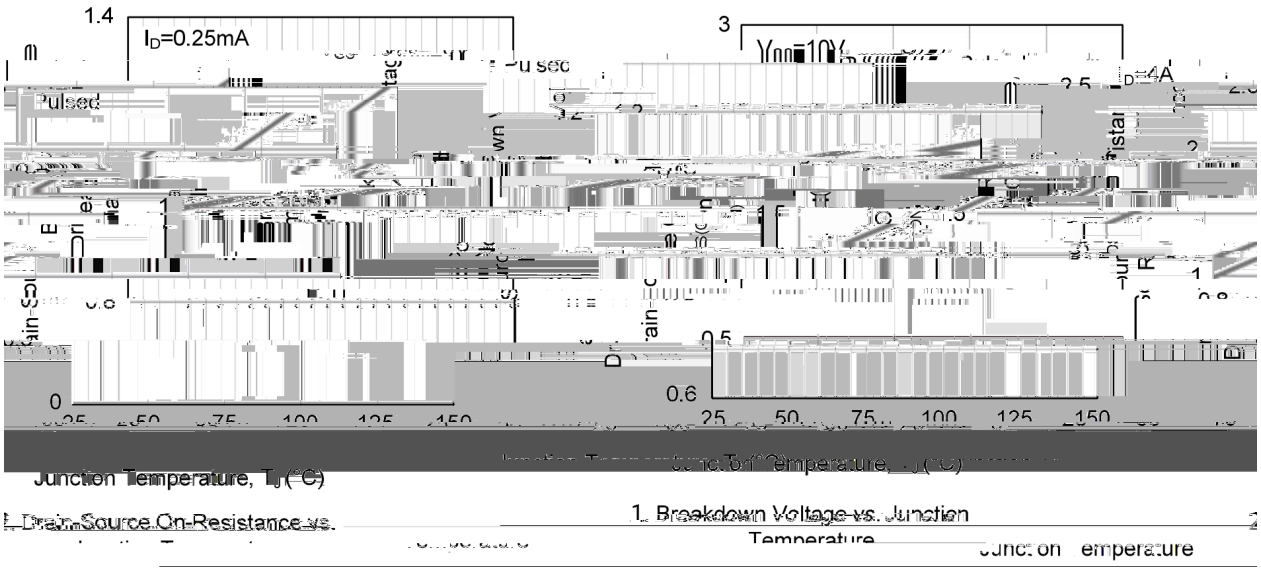
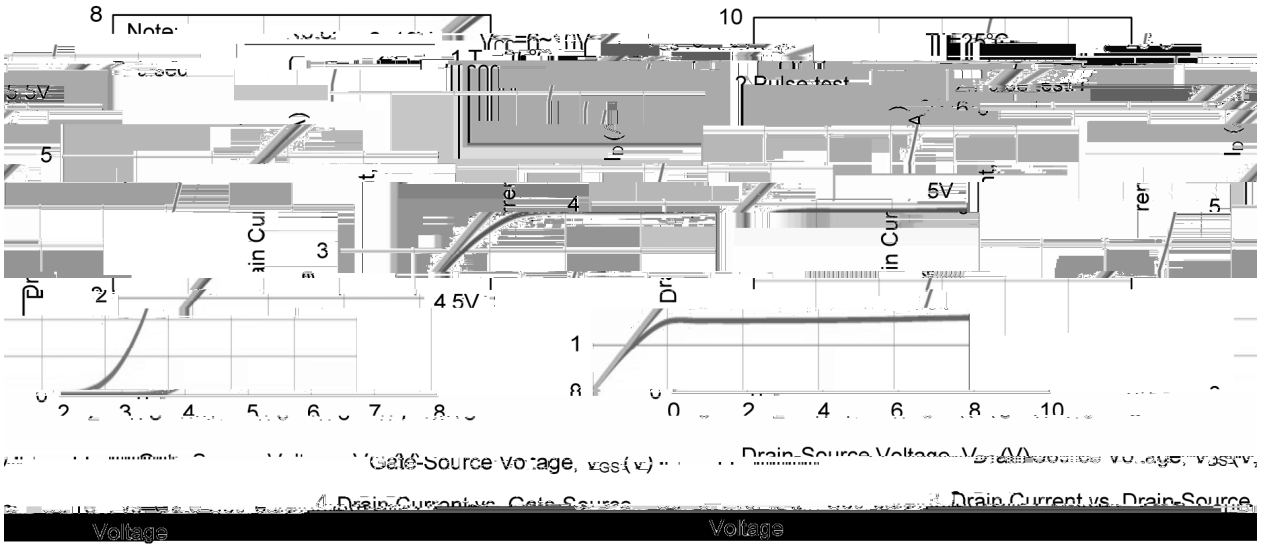
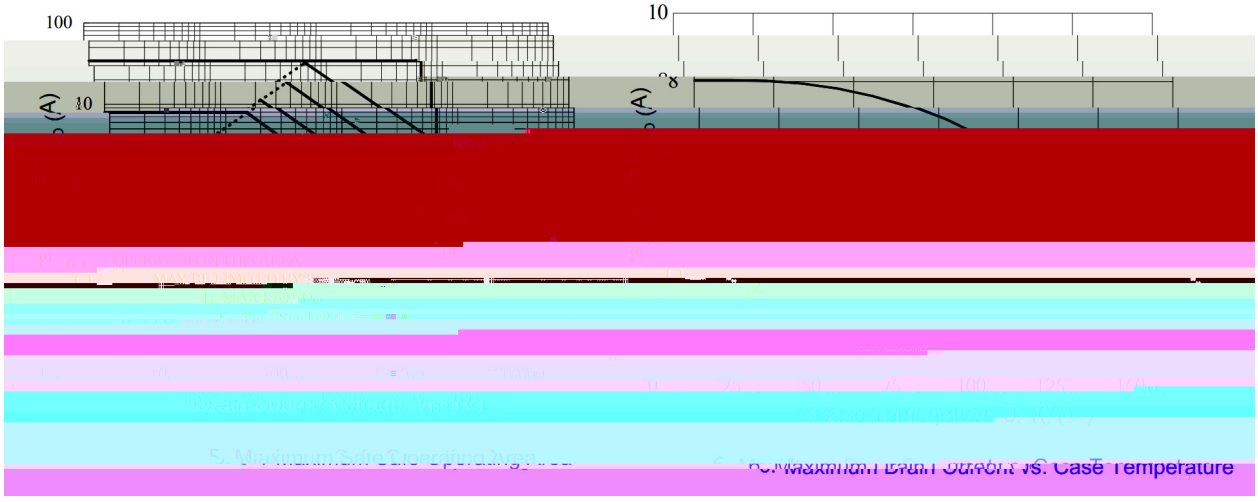
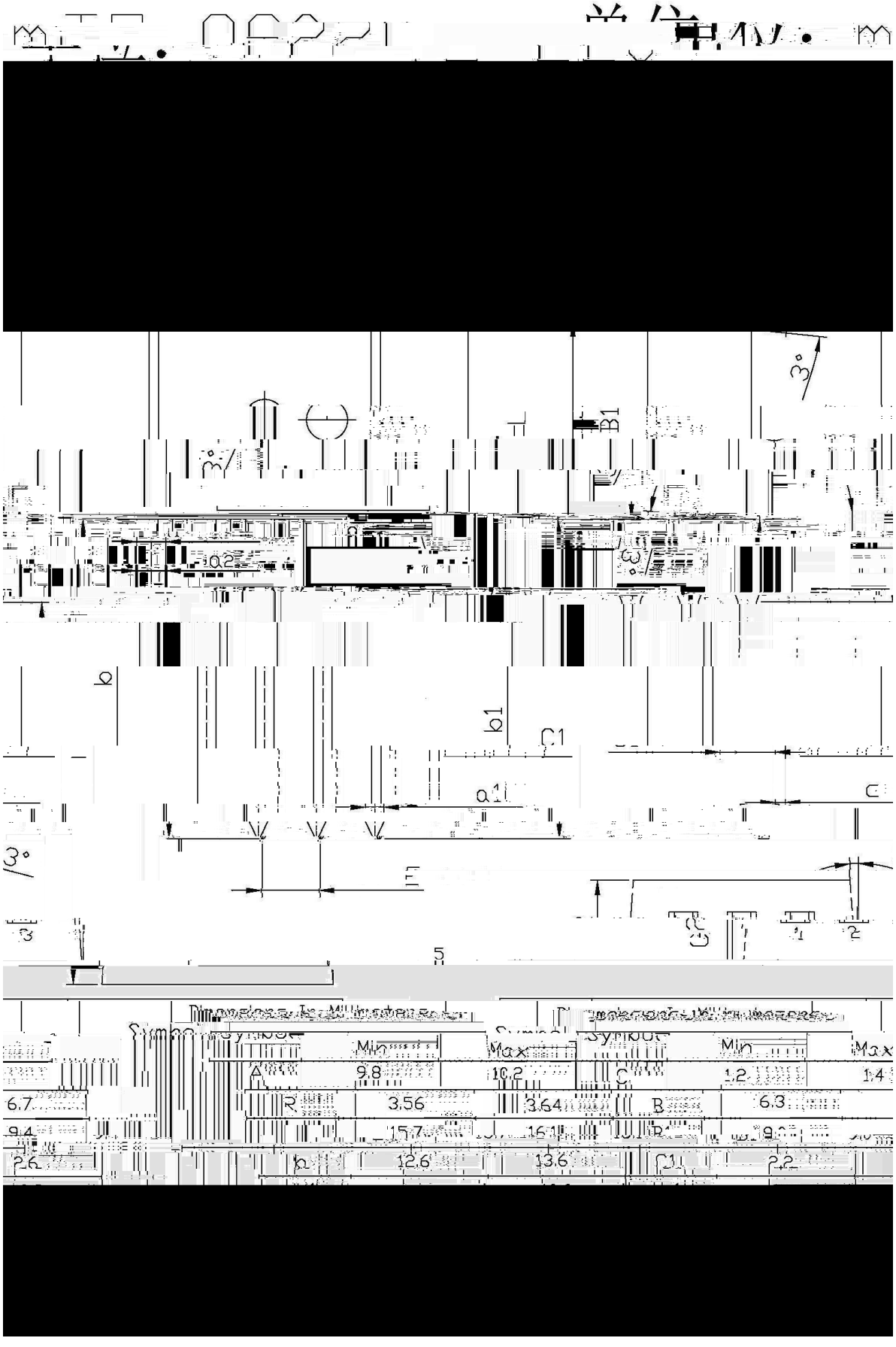


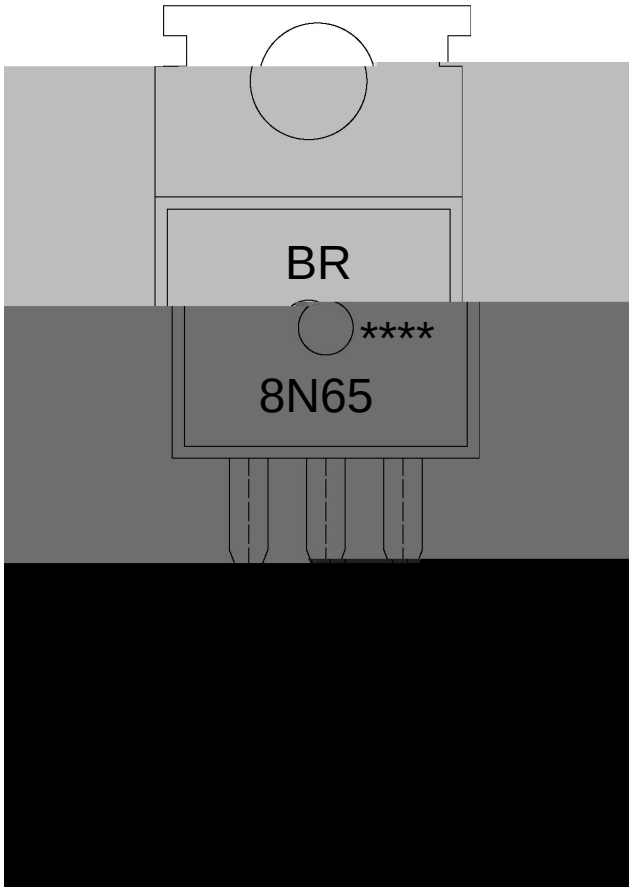




ᵘ ĖÒĻ ƒ / Package Dimensions



ł. Ļ'Ω / Marking Instructions



BR

8N65

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Note:

BR:	Company Code
8N65:	Product Type Code
****:	Lot No. Code, code change with Lot No

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